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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	10/714,612
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		First Named Inventor	Takashi UDAGAWA
		Art Unit	Not Yet Assigned - 2815
		Examiner Name	Not Yet Assigned - Landau
		Attorney Docket Number	Q73669

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Patent Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Number	Kind Code ² (if known)		
ML		US 3,054,936		09-18-1962	WILLIAMS et al.
ML		US 3,022,452		02-20-1962	WILLIAMS et al.

FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No. ¹	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Translation ⁴
		Country Code ³	Number ⁴	Kind Code ² (if known)			
ML		JP	2001-168395		06-22-2001	SHOWA DENKO KK	Abstract
ML		JP	2002-270896		09-20-2002	SHOWA DENKO KK	Abstract
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ML		JP	10-242569		09-11-1998	TOSHIBA CORP	Abstract
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NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation ⁴
ML		Japanese Search Report for PCT/JP03/14597 dated January 20, 2004 (Japanese language)	NO
ML		P. POPPER, et al.; "Boron phosphide, a III-V Compound of Zinc-Blende Structure"; Nature; No. 4569, May 25, 1997, p. 1075	
ML		J. PERET; "Preparation and Properties of the Boron Phosphides"; Journal of The American Ceramic Society, Vol. 47, No. 1, January 1964; pp. 44-46	
ML		Takao TAKENAKA et al.; "Diffusion Layers Formed in Si Substrates during the Epitaxial Growth of BP and Application to Devices"; Journal of Electrochemical Society, Vol. 125, No. 4, April 1978, pp. 633-636	NO
ML		K. SEEGER; "Semiconductor Physics, An Introduction"; Fourth Edition, Springer-Verlag Heidelberg, 1989	NO
ML		K. SHOHNO; "Semiconductor Techniques", 9th issue, University of Tokyo Press, pp. 74-77	NO
ML		T. IZUMIYA; "Growth of BP and GaN/BP heterostructures"; Phys. Conf. Ser., No. 129, 1993, pp. 157-162	
ML		I. AKASAKI; "Group III-V Compound Semiconductor"; Baifukan Co., Ltd., first edition, Chapter 13	NO
ML		K. SHOHNO, et al.; "Epitaxial Growth of BP Compounds on Si Substrates Using the B ₂ H ₆ -PH ₃ -H ₂ System"; Journal of Crystal Growth, 24/25, 1974, pp. 193-196	
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ML		Y. KUMASIRO, et al.; "Preparation and Electrical Properties of Boron and Boron Phosphide Films Obtained by Gas Source Molecular Beam Deposition"; Journal of Solid State Chemistry, Vol. 133, 1997, pp. 269-272	
ML		I. AKASAKI; "Group III Nitride Semiconductor"; Baifukan Co., Ltd., first edition, Chapters 13 and 14	NO

Examiner Signature	<i>Matthew C. Johnson</i>	Date Considered	4/4/05
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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